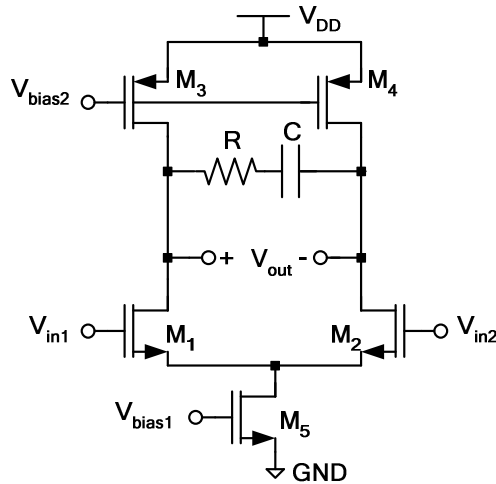


EECE488 Analog CMOS Integrated Circuit Design
Assignment 3
Due: Tuesday March 22nd, 2011 at 9:30am

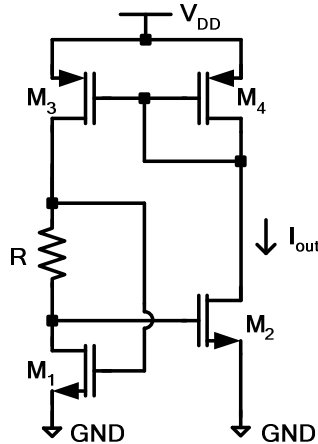
1. In the following circuit assume transistors M_1 and M_2 , and transistors M_3 and M_4 are identical and $\gamma = 0$; and $\lambda \neq 0$:

- i) Find the expression for the small-signal differential voltage gain ($\frac{V_{out}}{V_{in1} - V_{in2}}$) of the circuit. [
- ii) What is the gain of the circuit at very low frequencies?
- iii) What is the gain of the circuit at very high frequencies?



2. Assuming that all transistors are in saturation, $\left(\frac{W}{L}\right)_3 = \left(\frac{W}{L}\right)_4$, and $\lambda = \gamma = 0$:

- i) Find an expression for I_{out} .
- ii) What would be the percentage change in I_{out} if V_{DD} is increased by 10%.
- iii) How would the expression for I_{out} derived in part (i) change if $\gamma \neq 0$ and why?



3. Design a two-stage op amp based on the topology shown below with the following design specifications:

- $V_{DD}=3\text{ V}$
- Total power consumption of 3 mW
- Output swing of 2.6 V
- Total gain of 1000
- $L = 0.4\mu\text{m}$ for all the device

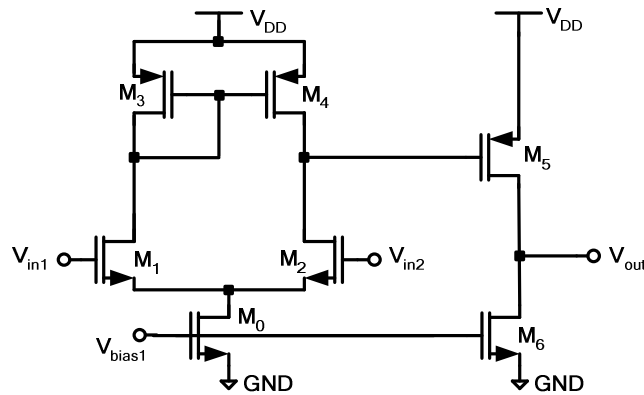
Use the following assumptions for your design

- Allocate equal overdrive voltages to M_5 and M_6
- Assume the bias currents of the first stage and the second stage are equal.
- $V_{SG3}=V_{SG5}$

The technology parameters are:

$\lambda_{(NMOS)} = \lambda_{(PMOS)} = 0.1\text{ V}^{-1}$, $\gamma = 0$, $V_{DD} = 3\text{ V}$, $V_{TH(NMOS)} = |V_{TH(PMOS)}| = 0.5\text{ V}$, $\mu_n C_{ox} = 1\text{ mA/V}^2$, $\mu_p C_{ox} = 0.5\text{ mA/V}^2$.

Note: Use the parameter λ only for calculating the r_o of the transistors. **Do not** use λ in any other calculation including your bias currents.



Find V_{bias1} , and all the transistor widths (i.e., $W_0, W_1, W_2, W_3, W_4, W_5, W_6$).